

Isc N-Channel MOSFET Transistor

SiHA11N80E

FEATURES

- With TO-220F package
- · Low input capacitance and gate charge
- · Low gate input resistance
- Reduced switching and conduction losses
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

· Switching applications

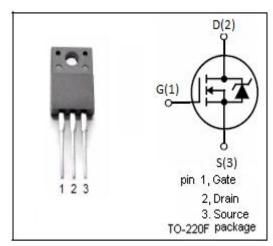


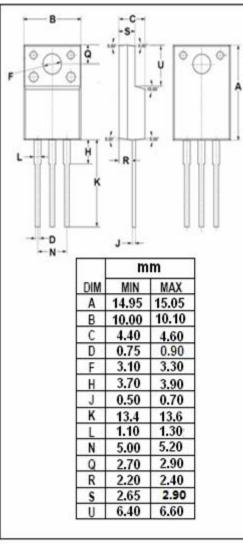
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	800	V	
V _{GSS}	Gate-Source Voltage	±30	V	
I _D	Drain Current-Continuous @Tc=25°C (V _{GS} at 10V) Tc=100°C	12 8	А	
I _{DM}	Drain Current-Single Pulsed	32	А	
P _D	Total Dissipation @Tc=25°C	34	W	
Tj	Max. Operating Junction Temperature	150	$^{\circ}$	
T _{stg}	Storage Temperature	-55~150	$^{\circ}$	

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	3.7	°C/W
Rth(ch-a)	(ch-a) Channel-to-ambient thermal resistance		°C/W







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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	800			V
$V_{\text{GS(th)}}$	Gate Threshold Voltage	V _{DS} = ±30V; I _D =0.25mA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =5.5A		380	440	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 800V; V _{GS} = 0V;Tj=25°C V _{DS} = 640V; V _{GS} = 0V; Tj=125°C			1 10	μА
V _{SDF}	Diode forward voltage	I _{SD} =5.5A, V _{GS} = 0 V			1.2	V

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